



NTE3123 Phototransistor Silicon NPN, Intermediate Acceptance, High Sensitivity, Darlington

Features:

- Epoxy Resin Package
- Compact
- Intermediate Acceptance: $\Delta\theta = \pm 40^\circ$ Typ
- Visible Light Cut-Off

Applications:

- VCRs
- Optoelectronic Switches

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Emitter Voltage, V_{CEO}	35V
Emitter-Collector Voltage, V_{ECO}	6V
Collector Current, I_C	50mA
Collector Power Dissipation, P_C	75mW
Operating Temperature Range, T_{opr}	-25° to $+85^\circ\text{C}$
Storage Temperature Range, T_{stg}	-40° to $+85^\circ\text{C}$
Lead Temperature, T_L	
During Soldering, 1.4mm from surface of resin edge, 3sec	$+260^\circ\text{C}$

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Current	I_C	$V_{CE} = 2V$, $E_v = 2\ell x$, Note 1	0.2	0.4	0.8	mA
Collector Dark Current	I_{CBO}	$V_{CE} = 10V$, $E_e = 0$	—	—	10^{-6}	A
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 0.8mA$, $E_e = 1mW/cm^2$, Note 1	—	—	1.0	V
Peak Emission Wavelength	λ_P		—	860	—	nm
Response Time (Rise)	t_r	$V_{CE} = 2V$, $I_C = 5mA$, $R_L = 100\Omega$	—	400	2000	μs
Response Time (Fall)	t_f		—	300	1500	μs
Half Intensity Angle	$\Delta\theta$		—	± 40	—	deg.

Note 1. E_e , E_v : Illuminance, irradiance by CIE standard light source A (tungsten lamp).

